

P-Channel 30-V (D-S) MOSFET

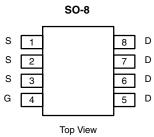
| PRODUCT SUMMARY | | | | |
|---------------------|----------------------------------|--------------------|--|--|
| V _{DS} (V) | $r_{DS(on)}\left(\Omega\right)$ | I _D (A) | | |
| -30 | 0.02 @ V _{GS} = -10 V | -8.0 | | |
| | 0.035 @ V _{GS} = -4.5 V | -6.0 | | |

FEATURES

• Lead (Pb)-Free Version is RoHS Compliant



COMPLIANT



Si4435DY-T1-A-E3 (Lead (Pb)-Free)

Ordering Information: Si4435DY-T1-REV A

P-Channel MOSFET

| G o — | |
|--------------|---|
| | D |

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ UNLESS OTHERWISE NOTED) **Parameter Symbol** Limit Unit Drain-Source Voltage V_{DS} -30 ٧ Gate-Source Voltage V_{GS} ± 20 $T_A = 25^{\circ}C$ -8.0 Continuous Drain Current (T_J = 150°C)^a I_D $T_A = 70^{\circ}C$ -6.4Α Pulsed Drain Current -50 I_{DM} Continuous Source Current (Diode Conduction)^a I_{S} -2.1 $T_A = 25^{\circ}C$ Maximum Power Dissipationa \mathbf{P}_{D} W $T_A = 70^{\circ}C$ 1.6 Operating Junction and Storage Temperature Range T_J , T_{stg} -55 to 150 ٥С

| THERMAL RESISTANCE RATINGS | | | | | | | |
|--|-------------------|-------|------|--|--|--|--|
| Parameter | Symbol | Limit | Unit | | | | |
| Maximum Junction-to-Ambient ^a | R _{thJA} | 50 | °C/W | | | | |

a. Surface Mounted on FR4 Board, $t \le 10$ sec.

For SPICE model information via the Worldwide Web: http://www.vishay.com/www/product/spice.htm



| SPECIFICATIONS (T _J = 25°C UNLESS OTHERWISE NOTED) | | | | | | | | |
|---|---------------------|--|------|-------|-------|------|--|--|
| Parameter | Symbol | Test Condition | Min | Тура | Max | Unit | | |
| Static | | | • | 1 | • | • | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = -250 \mu A$ | -1.0 | -2.0 | -3.0 | V | | |
| Gate-Body Leakage | I _{GSS} | V_{DS} = 0 V, V_{GS} = ± 20 V | | | ± 100 | nA | | |
| Zero Gate Voltage Drain Current | | $V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$ | | | -1 | μΑ | | |
| | IDSS | $V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70^{\circ}\text{C}$ | | | -5 | | | |
| | | $V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$ | -40 | | | А | | |
| On-State Drain Current ^b | I _{D(on)} | $V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$ | -10 | | | | | |
| D : 0 | | $V_{GS} = -10 \text{ V}, I_D = -8.0 \text{ A}$ | | 0.015 | 0.02 | Ω | | |
| Drain-Source On-State Resistance ^b | r _{DS(on)} | $V_{GS} = -4.5 \text{ V}, I_D = -5.0 \text{ A}$ | | 0.022 | 0.035 | | | |
| Forward Transconductanceb | 9fs | $V_{DS} = -15 \text{ V}, I_D = -8.0 \text{ A}$ | | 20 | | S | | |
| Diode Forward Voltage ^b | V _{SD} | $I_S = -2.1 \text{ A}, V_{GS} = 0 \text{ V}$ | | -0.75 | -1.2 | V | | |
| Dynamic ^a | | | | | | | | |
| Total Gate Charge | Qg | $V_{DS} = -15 \text{ V}, \ V_{GS} = -10 \text{ V}, \ I_D = -4.6 \text{ A}$ | | 47 | 60 | nC | | |
| Gate-Source Charge | Q _{gs} | | | 9.5 | | | | |
| Gate-Drain Charge | Q _{gd} | | | 8 | | | | |
| Gate Resistance | R _G | | | 2.75 | 4.1 | Ω | | |
| Turn-On Delay Time | t _{d(on)} | $V_{DD} = -15 \text{ V, } R_L = 15 \Omega$ $I_D \cong -1 \text{ A, } V_{GEN} = -10 \text{ V, } R_G = 6 \Omega$ | | 16 | 30 | ns | | |
| Rise Time | t _r | | | 17 | 30 | | | |
| Turn-Off Delay Time | t _{d(off)} | | | 75 | 120 | | | |
| Fall Time | t _f | | | 31 | 80 | | | |
| Source-Drain Reverse Recovery Time | t _{rr} | $I_F = -2.1 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$ | | 40 | 80 | | | |

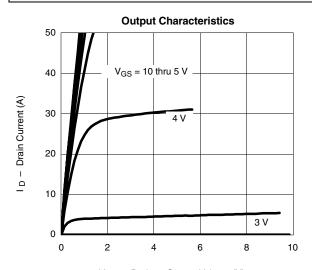
Notes

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

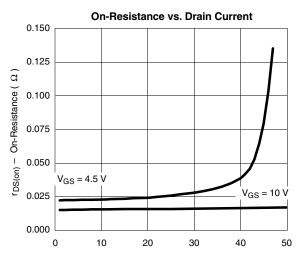
Guaranteed by design, not subject to production testing. Values shown are for Product Revision A. Pulse test; pulse width $\leq 300~\mu s$, duty cycle $\leq 2\%$.



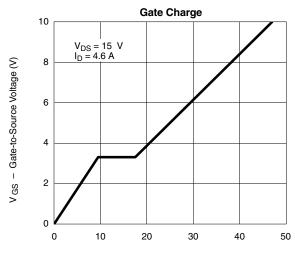
TYPICAL CHARACTERISTICS, PRODUCT REVISION A (25°C UNLESS NOTED)



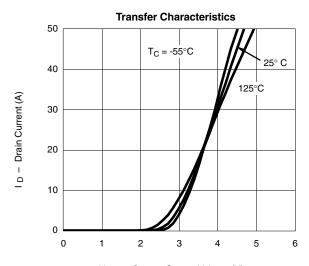
 $V_{DS}\,-\,$ Drain-to-Source Voltage (V)



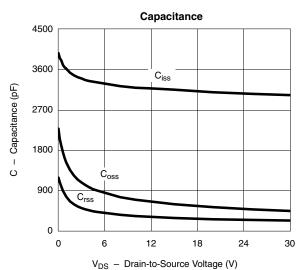
I_D - Drain Current (A)

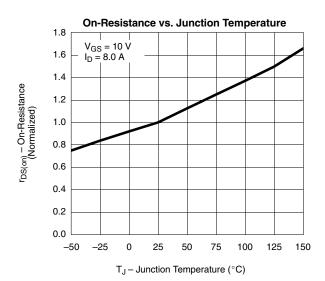


Q_q - Total Gate Charge (nC)



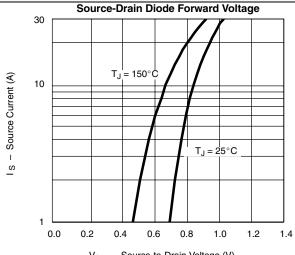
V_{GS} - Gate-to-Source Voltage (V)

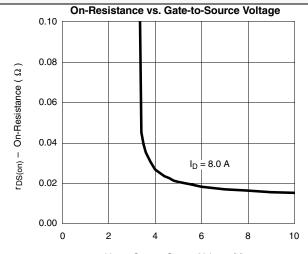


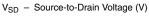


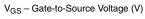


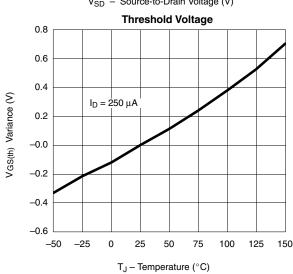
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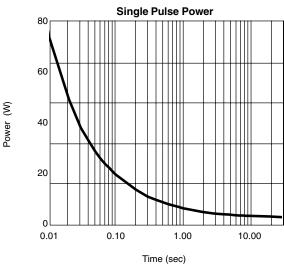


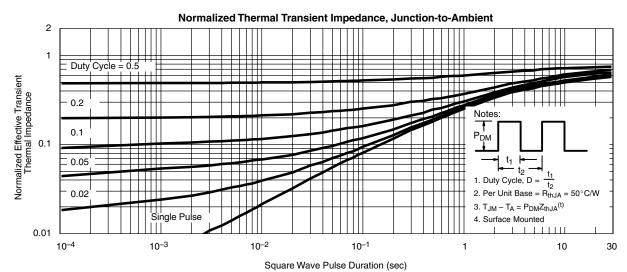












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